

EXERCISES
Computational Materials Science

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SHEET 4

Exercise 4: Coherent potential approximation

In this exercise the tight-binding model for PbVO_3 shall be supplemented by a bipartite disorder potential $\pm\epsilon/2$ of equal probability. Remind that, within DFT, PbVO_3 has a single band near the Fermi level that is well described by the tight-binding energy-momentum relation

$$\epsilon_{\mathbf{k}} = \epsilon_0 + 2t_1 (\cos(k_x a) + \cos(k_y a)) + 4t_2 \cos(k_x a) \cos(k_y a) \quad (1)$$

with $a = 3.8\text{\AA}$, $\epsilon_0 = 0.03\text{eV}$, $t_1 = -0.154\text{eV}$ and $t_2 = -0.05\text{eV}$.

Task 1)

Write a program to solve this disorder problem using the coherent potential approximation (CPA).

Task 2)

Study the spectral function (density of states) as a function of ϵ for a) $\epsilon_0 = 0$, $t_2 = 0$, $\mu = 0$ and b) the values for PbVO_3 . At which disorder strength ϵ does a metal-insulator transition occur? Which \mathbf{k} -, ω -grid, δ did you choose?

For going beyond, i.e. for the (exam) talk

For example you may (i) study convergence w.r.t. to the \mathbf{k} -, ω -grid and δ ; (ii) consider other disorder distributions or other lattices; (iii) study a doped model and/or adjust μ to a fixed number of particles; determine the self energy in the limit of (iv) weak or (v) strong disorder strength and compare with the exact solution. An other alternative (vi) is to treat the Hubbard model with local interaction U using the dynamical mean field theory (DMFT) where the impurity problem becomes an Anderson impurity model (we would provide an impurity solver).